

BAE SYSTEMS

Advanced Microprocessor Technologies

and Challenges for Space Applications

Nadim F. Haddad

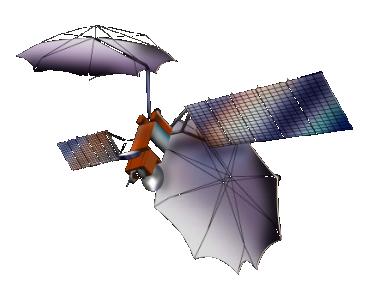
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2001 IEEE Microelectronics Reliability and Qualification Workshop

December 11-12

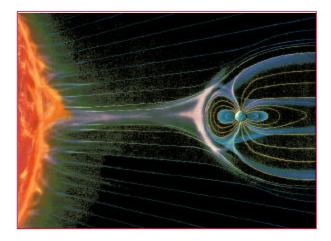
Pasadena, CA





- The Environment
- Effect of Technology Migration
- Mitigation Schemes and Penalties
- Radiation Hardened Processors for Space
- Space Processor Roadmap
- Conclusion





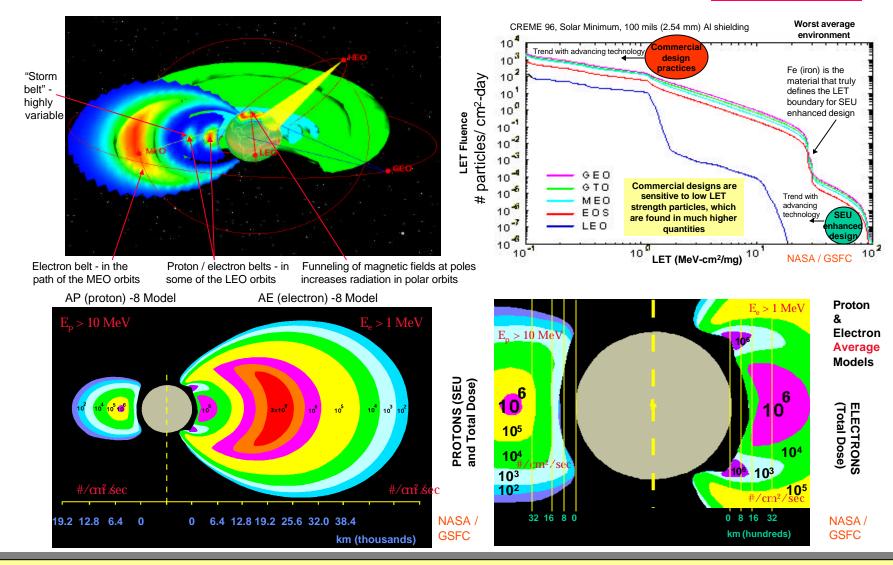
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Nikkei Science, Inc. of Japan, by K. Endo

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Variations in Radiation Flux Density

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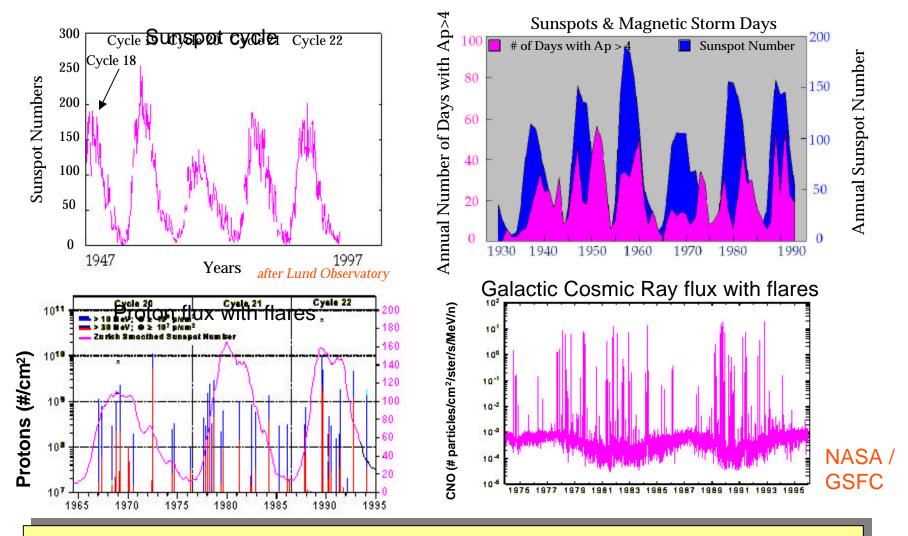


Variability of radiation environments affects the applicability of COTS in space

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Extreme Conditions - Solar Flares

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Space environment is very variable - solar flares are unpredictable and create a severe environment

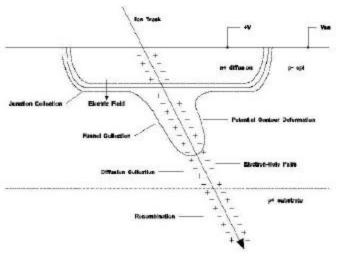
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Issues Associated with Space

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- Radiation environment
 - <u>Total lonizing Dose</u> (TID) accumulation of radiation over time
 - Prompt Dose ability to function during a massive burst of radiation
 - <u>Survivability</u> ability to function after a massive burst of radiation
 - <u>Single Event Effects</u> (SEE) soft or hard errors as the result of the penetration of a single charged particle
 - <u>Single Event Upset</u> (SEU) state change of a storage node
 - <u>Single Event Transient</u> (SET) pulse injection into combinational logic
 - <u>Single Event Gate Rupture</u> (SEGR) destruction of the gate of a transistor
 - <u>Single Event Latchup</u> (SEL) "lock-up" of a device; must remove power to reset
 - <u>Single Event Burnout</u> (SEB) Burnout, especially in power devices

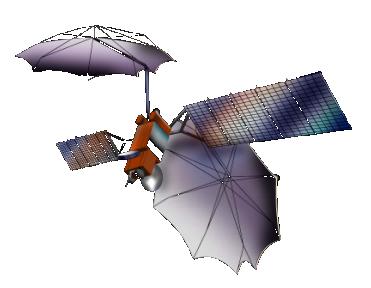
- Wide temperature range and stresses
- High reliability
- Mechanical stresses
- Severe mass and power constraints



Charge from single event impact

Spacecraft electronics are expected to overcome severe environmental conditions





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Trends in Commercial Technology



	Commercial CMOS Technology				<u>ogy</u>	У		
Environment	0.8 m m	0.5 mm	0.35 m m	0.25 m n	0.18 m m	0.13 mm	0.18 mm SOI	<u>Hard</u>
Total Dose (Krad(Si))	10 - 20	20 - 40	20 – 50	40 - 100	40 - 150	40 – 150	30 – 50	200 – 1,000
SEU (u/b-d) (90% W.C. Geo)	1E-7	1E-6	2E-6	5E-6	1E-5	>1E-5	1E-6 to 1E-7	< 1E-10
Prompt Dose Upset (rad/s)	1E7	1E7-1E8	1E7-1E8	1E7-1E8	1E7	<1E7	1E8	> 1E9
Latch up	Generally prone	Some prone	Some prone	Generally immune	Generally immune	?	Possibly self-latch	Immune
Neutron (u/cm ²)	1E14 (limited by TID)	1E14 (limited by TID)	1E14	1E13- 1E14	?	?	?	1E14

Trends in commercial technologies have not always been favorable for spaceborne application, given the various failure mechanisms

Effect of Scaling on Single Event Upset **BAE SYSTEMS** SIZE DURATION STRENGTH Diffusion 1.0um node $\wedge V = \wedge Q/C$ @ 5 MHz, pulse = 100 ns.0.18um Nodal cap < 1/10xתוקהאקרוקוקוקוקות הקה הקורקהוקוקה הקורקוקה הקה הקה הקורקוקוקוקוקו Current drive < 1/3x@ 500 MHz, Charge pulse = 1 ns.Therefore, susceptibility of collection 1.0µm CMOS to an area LET=10-20 translates to SEU Pulse = 0.3 ns. susceptibility of 0.18 µm

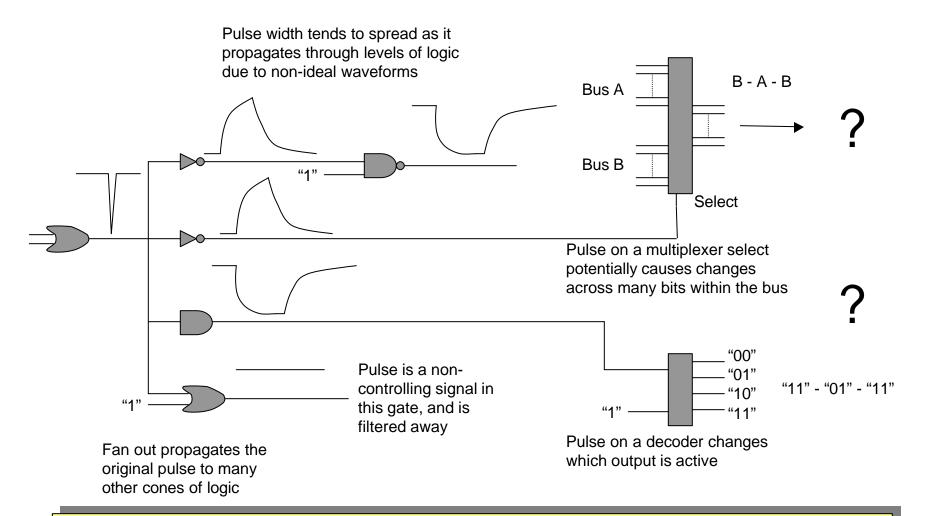
Technology scaling is driving a multi-exponential increase in sensitivity to SEU / SET

CMOS to an LET = 0.3-0.7

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Single Event Transient (SET)

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An injected pulse can propagate far beyond it's point of inception, based on logic design paths

SEU Susceptibility in Dynamic Circuitry

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- Global block select decoder
- Classic pre-charged dynamic circuit used in: decode, buffers, datapaths, logic, and clocks
- Operation:
 - CLOCK = "0" results in output pre-charge to "1"
 - CLOCK = "1" results in valid signal output, based on input conditions
- Very soft, due to:
 - Small bleeder device holding "1" state
 - Switching due to SET pulse on clock line
- Upset will select wrong block of data (1 block = 32K bits)

VDD IB4 S G G Q CLOCK ■ CLOCK ■	Tiny "bleeder" device holds output to "1" S [183 AØ X O BLOCK	<_SEL
	Clock line and devices dynamically control output state	
B ■ G A B ■ G A IB8 D IB8 D C ■ G A	Input devices configured as 3-input NAND	
GNC	ranene enen enen enen enen enen enen eren eren eren eren bieten beide bezen bei bezen eren bieten beid bezen b Kalen beid bezen beid beid beide beid beide beid beide beide beid bezen beid bezen beid beide beid beide beid Tenens beid beides beid beid beide beid beide	

Exotic circuit design techniques (common in recent COTS products) increase density and performance, but are more susceptible to SEU/SET

Estimated SEU Rates by Commercial Processor Generation

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	RSC - "G0(?)"	601 - "G1"	603 / 603e - "G2"	750 - "G3"	7400 - "G4"
	Fechnology: 0.8 μm Fransistors: 1.0 M Supply: 3.6 V Speed: 33 MHz Released: 1992	0.6 µm 2.8 M 3.6 V 50 MHz 1993	0.5 / 0.35 µm 1.6 / 2.6 M 3.3 V / 2.5 V 80 MHz / 200 MHz 1994 / 1995	0.25 µm 6.4 M 2.5 V 266 MHz 1997	0.18 µm 10.5 M 1.8 V 450 MHz 1999
ç	Estimated SEU Rate 90% GEO: 1 / 60 days During Flares: 0.02 - 2 / min	1 / 8 days 0.1 - 9 / min	1 / 5 days / 1 / day 0.2 - 14 /min / 1 - 100 / min	1 / hour 0.3 - 27 / sec	3 / hour 1 - 100 / sec

* SET upsets begin to increase at 0.35 micron and then accelerate, due to small devices, low supply, and high clock rates

Across Generations, the Increase in SEU/SET Susceptibility is Dramatic

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Total Dose Mitigation



Total Dose Environment for Various Orbits (10 Year Mission Assumed)						
Or	<u>bit</u>	Total Dose (krad(Si))				
Altitude(Km) Inclination(Degree)		<u>100 mil Al</u>	<u>250 mil Al</u>			
850	28	22	12			
1,350	90	56	38			
1,400	53	130	50			
1,500	30	240	100			
Geo	00	400	20			
1/2Geo	60	3,000	100			

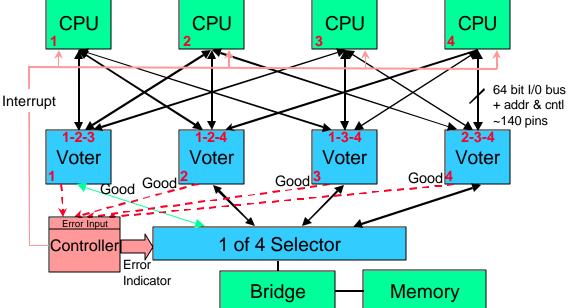
Shielding is an effective way to reduce total dose, but it comes at a cost... It is also ineffective in mitigating single event effects

SEU Mitigation - Redundant System Example

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Hardware redundancy functions

- Multiple voting functions check the CPU outputs, confirming correct results or identifying the "bad" CPU
- If a fail is detected:
 - The controller uses that information to shut down (hard reset) the failing CPU
 - Begins recovery routine
- The selector sends good output to the I/O and/or memory
- Approximately two cycles of latency are added to I/O and memory operations



• Software redundancy functions

- Regular "sweep" issued to cause output for checking
- Either clears key embedded memories (caches, branching) during each regular sweep, or during a recovery operation
- Match up the processors at a "work task" boundary, and start simultaneous processing again

Redundant systems operate by detecting errors in processing functions after they occur and removing them through voting

Applicability of Redundant COTS Electronics in Space

Orbital variations

- Low LEO is the most benign (below 800 km)
- Polar more severe than near equatorial
- Upper LEO is more severe for both Total Dose and SEU
- The South Atlantic Anomaly is the worst case in LEO orbits
- MEO is worst for Total Dose
- GEO is worst for Cosmic Rays
- Long term missions encounter extreme conditions at some point (solar flares and coronal mass ejections); these conditions REQUIRE SEU immune design redundancy is not applicable

Application variations

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- Short term applications (example: shuttle) may be timed around extremes
 - Some unpredictability exists
 - Some years are better than others
- Applications that can accept outages (1-4 days in length) can simply shut down during solar flares (example: geology, telescope)
- New ASIC designs can address some of the problem in design
 - TMR at each latch
 - Error correct embedded memories
 - Addressing SET errors is more difficult
- Real time / critical applications have a problem; they CAN'T shut down (example: cell phone, internet, video, weather, global positioning, military)

The Ability to Consider TMR is a Function of Both Orbit and Application

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Redundant Modern Commercial Processors in Space

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Size, weight, and power (SWAP)

• Size

- TMR requires significant board space
 - 3-4 CPUs
 - Voting Chip
- Will not fit on a 3U format

• Weight

 About 2X weight of Single Processor Solution

• Power

- Increased Component Count
- Increased processing for upset checking / recovery
- About 3X Power

Software effort and overhead

- Effort
 - "Upset checking" routine
 - Split application code for regular checking
 - Recovery routine

Overhead

- Interrupted processing
- Increased check pointing
- 50% Performance loss Typical
 - (through HW & SW)

<u>SEU / SET</u> susceptibility

- Upset mechanisms
 - Dynamic logic
 - Storage nodes
 - Transient (SET) propagation

• Flux rate

- GCR Cause 1-2 upsets / hr
- Protons at LEO cause
 0.3-0.7 upsets / hr
- Solar flares cause 0.1 20 upsets / sec

Recovery

- TMR recovery will typically require several minutes
- Upsets may not be detected in time to respond
 Expect trouble during
- flares

Product cost

Component costs

- Rad-hard voting chip has high recurring cost in addition to NRE
- Commercial CPUs have cost advantage

Software costs

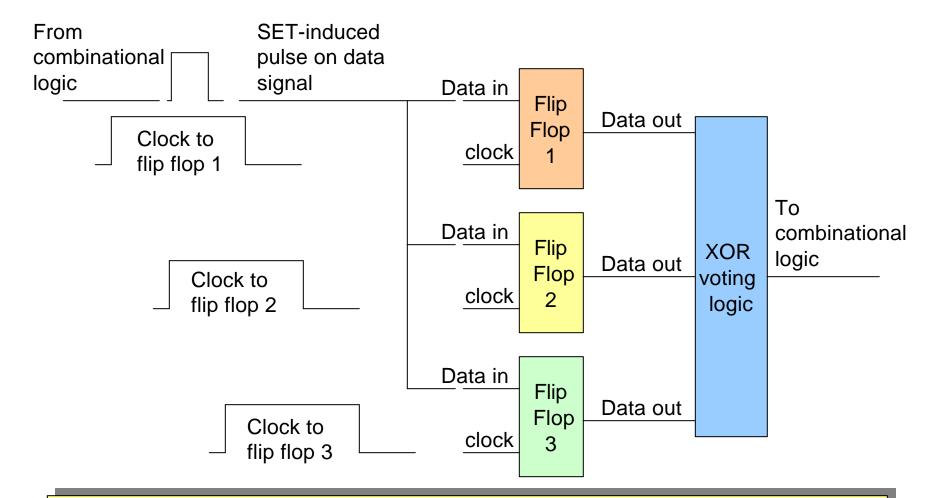
- NRE for development of checking and recovery routines
- Board costs

More complex board design with lead time vs. a standard radhard product

Commercial Processors, Even with Redundancy, Have Issues and Exposures that Far Outweigh their Benefits Compared to Enhanced Processor Solutions

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SEU Mitigation - Redundant Circuitry Example BAE SYSTEMS



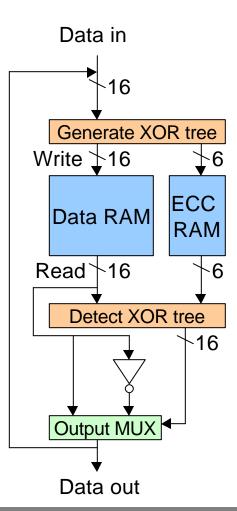
Redundant storage cells with time shifted clocks fight SET upsets by attempting to filter out the pulse prior to capturing it

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SEU Mitigation - In-line Error Correction

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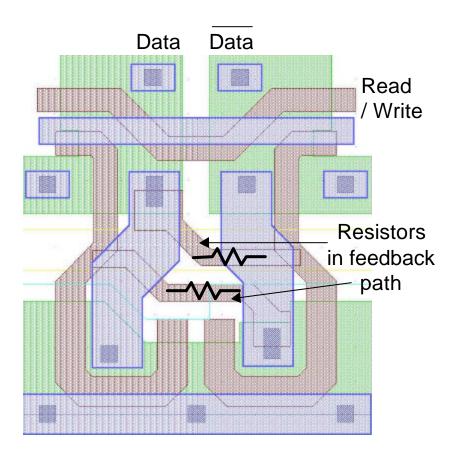
- Typical uses
 - Memory subsystems
 - Communication links
- Sequence for Single Error Correct Double Error Detect (SECDED):
 - Generate error bits via XOR based on masking
 - Detect error via XOR with masking
 - No mismatch indicates good data
 - Valid value identifies bit in error
 - Invalid value defines uncorrectable errors
 - Multiplex data or inversion bit-by-bit to correct
- Radiation mitigation:
 - Employ variable rate "scrubbing" (read, test, correct and write back if needed) sequence at varying rates, based on rate of errors induced
 - Useful until error rate exceeds ability to fix or ability to perform both function and correction
 - Combination with hardened Cache reduces functional access demand

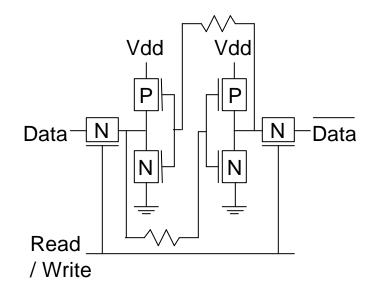


Error correction removes errors that occur within stored memory by generating codes that uniquely identify the validity of each bit of data

SEU Mitigation - Hardened Circuitry Example

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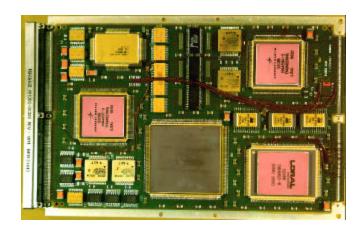
- Large resistance in the feedback path fights state change in the cell via RC time constant
- Typically employs unique manufacturing process steps
- Adverse effects on Write time and circuit density

Radiation hardened circuits prevent upsets through design techniques that fight against the charge deposit from the impact

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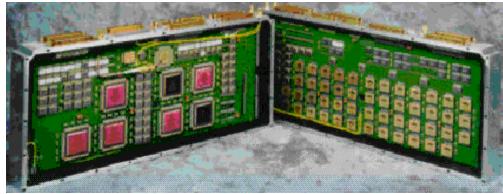


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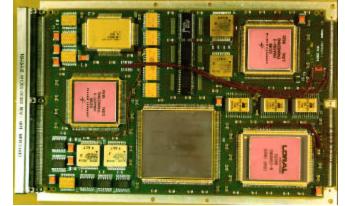
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90 satellites currently on orbit with 286 single board computers*

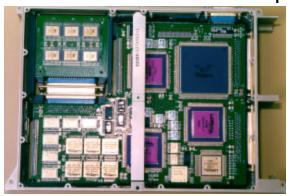
* As of November 30, 2001



Cassini GVSC processor



SBIRS Low/Orbview RAD6000™



CCP drop in tray (GVSC) Over 500 flight boards delivered or ordered for new launches through 2006



VME 6U RAD6000TM board * * as used on FHLP

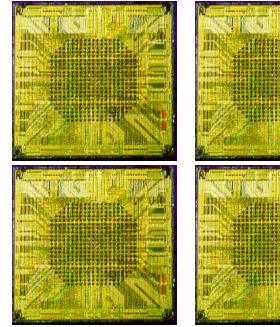
Our processors have been the standard in space for many years, with millions of hours of flawless operation in a variety of applications

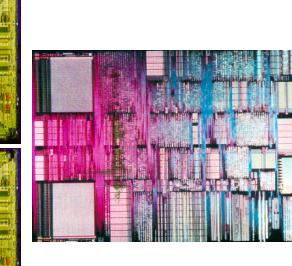
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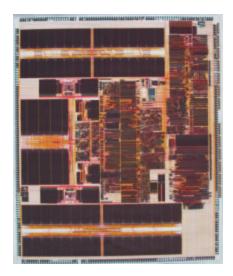
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Three generations of radiation hardened microprocessors

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- 1991 GVSC 1750 1.0 μm Radiation Hardened CMOS – MIL-STD-1750A architecture – 4 by 88 sq mm – 0.3 M transistors
- 20 MHz
- 3 MIPS

1996 RAD6000™

- $0.5\ \mu m$ Radiation Hardened CMOS
- RS/6000 "Power" architecture
- 145 sq mm
- 1.1 M transistors
- 33 MHz
- 35 MIPS

2001 RAD750™

 $0.25\,\mu m$ Radiation Hardened CMOS

- PowerPC architecture family

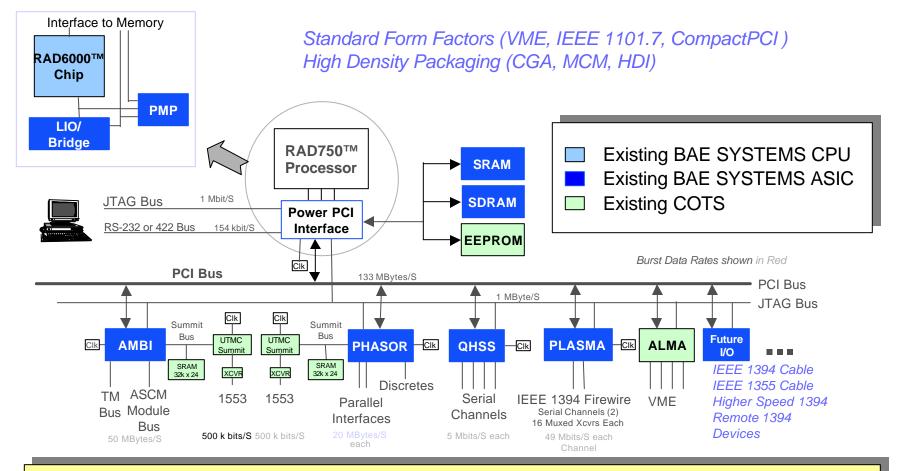
– 130 sq mm

- 10.4 M transistors
- 133 166 MHz (up to 200 as available)
- -240 300 MIPS (up to 366 as available)

The RAD750 represents our third generation product, with architectural and technological enhancements that improve power/performance

RAD750[™] - Power PCI RAD6000[™] architecture compatibility





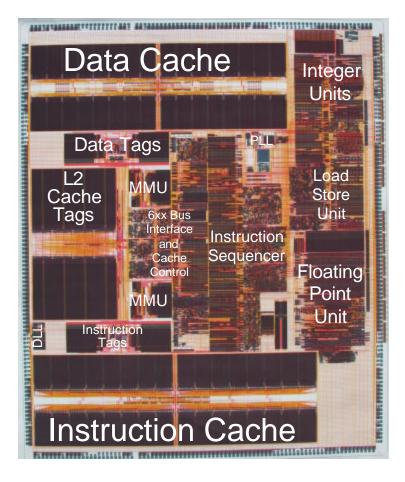
The RAD750[™] and Power PCI easily replace the current RAD6000[™] and LIO in our processor board architecture

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RAD750[™] specifications

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Specifications	
Processor Speed	110 to 133 MHz
Process Technology	0.25 um (0.18 um Leff) CMOS, 6 levels of metal
Die Size	10.4 mm. by 12.5 mm.
RAD750™ Performand without L2 (est) with 1MB L2 (est)	e 6.5 SPECint95 3.9 SPECfp95 @ 150 MHz. 7.0 SPECint95 4.7 SPECfp95 @ 150 MHz.
Signal I/O	256 (including L2 port)
Power Supply	2.5 V + / - 5% core 2.5 or 3.3 V + / - 10% I/O
Power Dissipation	5.0 watts at 133 MHz, 2.5V
Temperature Range	-55°C to +125°C
Packaging	25.0 mm. by 25.0 mm. by 6.22 mm. 360 pin Column Grid Array (CGA)
Mass	9.0 grams
Radiation Hardness	Total Ionizing Dose: 200 Krad (Si) SEU: 1E-10 upsets / bit-day (W.C. 90% GEO) Latchup: Immune
Mean Time Between Failures (MTBF)	> 4.3M hours



The final design has completed characterization and qualification

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RAD750[™] Testing Status

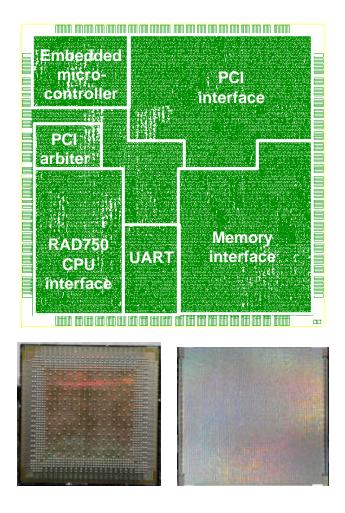
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- RAD750[™] Testing was completed October 31 (functional equivalency to PowerPC[™] 750 verified)
- Environmental testing proved successful across the full military temperature and voltage ranges
- Performance specification will be 110 MHz 133 MHz based upon screening levels
- Radiation testing results support flight requirements
 - No latchup nor gate rupture
 - -TID >200Krad(Si)
 - SEU <1E-10 error/bit.day
 - Threshold LET(@10% of Saturation) = 45 MeV/mg/cm²
- RAD750[™] Specification Updated to reflect testing

Power PCI ASIC specifications

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Specification	IS
Clock Speed	33 MHz
Process Technology	0.50 um Leff CMOS, 5 levels of metal
Die Size	12.7 mm. by 12.7 mm.
Cells / Gates / Latches	926K / 700K / 26K
PCI Peak Bandwidth	130 MB/s write 90 MB/s read
Signal I/O	456 (+ <i>test</i>)
Power Supply	3.3 V + / - 10% core and I/O
Power Dissipation	1.5 W
Temperature Range	-55°C to +125°C
Packaging	32.5 mm. By 32.5 mm. By 6.22 mm. 624 pin Column Grid Array (CGA) with flip-chip C4 mount
Radiation Hardness	Total Ionizing Dose: >1Mrad (Si) SEU: < 1E-10 upsets / bit-day (W.C. 90% GEO) Latchup: Immune
Mass	14.5 grams



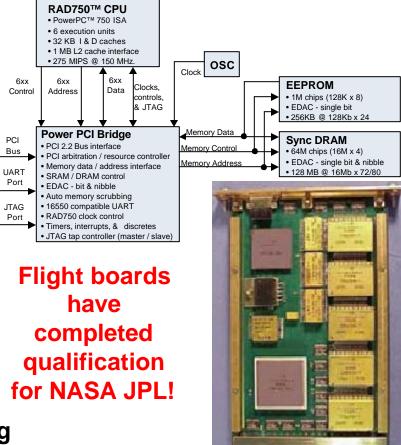
The Power PCI has been integrated on a 3U CompactPCI single board computer

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Conduction Cooled CompactPCI® 3U Format RAD750[™] Processor Board

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Specifications	
Form Factor	CompactPCI 3U (100 mm x 160 mm.) Weight: 549 grams
Processor	RAD750 [™] 240 Dhrystone 2.1 MIPS @ 133 MHz.
Radiation Hardness	Total Ionizing Dose: > 100 Krad (Si) SEU: < 1E-5 upsets/day (W.C. 90% GEO) Latchup: Immune
Performance (estimated)	5.8 SPECint95 3.5 SPECfp95 @ 133 MHz.
PCI Backplane Bus	32 bit, 33 MHz., PCI version 2.2 Peak Bandwidth: 130 MB/s write 90 MB/s read Can be keyed for System or Agent Slot
Power Supply	3.3 V + / - 10% (2.5 V generated via on-board regulator)
Power Dissipation (typ)	10 W
Temperature Range	-55°C to +125°C
Mean Time Between Failures (MTBF)	Greater than 390K hours



Currently available in flight, engineering and low cost commercial versions

The RAD750[™] product line introduces a completely new era of both onboard processing capability and space standard products

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RAD750[™] Software Development Environment BAE SYSTEMS



Software Development System

- Pentium personal computer
- Windows NT Operating System
- Ethernet connection to RAD750
- Corellis JTAG interface
- RAD750 or COTS PowerPC Board

Green Hill Multi and GNU Tools

- Optimized C, C++, Ada compilers
- Source level debugger
- Mixed language integration
- Version control system
- Program builder
- Editor

WindRiver VxWorks OS

- High performance multi-tasking kernal
- Networking capability
- Device independent I/O
- Dynamic load of user programs
- Highly configurable execution environment
- "Tornado" Software development and debug tools

BAE SYSTEMS Supplied Software

Board Support Package (BSP)

• VxWorks compatible

I/O device drivers Start-Up ROM (SUROM)

- System "Reset handler"
- On-board diagnostics
 - CPU and Power PCI self-test
 - Memory test
- Bootstrap image load into RAM
- Test and initialize board hardware
- Fault recovery during restart

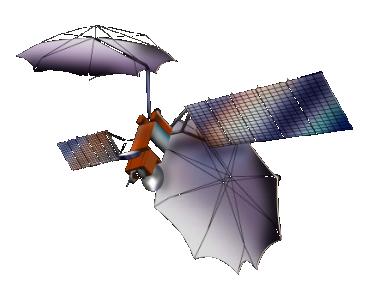
A complete environment, based on our RAD6000[™] experience, eases RAD750[™] software development

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Hardened Processor Flight Heritage

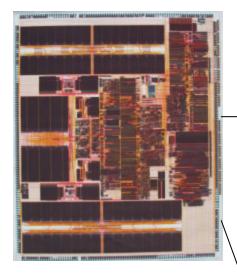
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(Launched)			(Under Contract)			(Under Contract /	Plan)	
<u>SATELLITE</u>	<u>SATs</u>	<u>SBCs</u>	<u>SATELLITE</u>	<u>SATs</u>	<u>SBCs</u>	SATELLITE	<u>SATs</u>	<u>SBCs</u>
Agila / APSTAR-2R	2	4	ChinaSat 8	1	2	Intelsat 903-905	3	12
Cassini	1	7	Globalstar (16 bit)	4	8	KaStar 1,2	2	4
EchoStar 5	1	2	Intelsat 902	1	4	Messenger	2	10
Garuda 1 (ACeS)	1	2	SS/L DBS-3	2	4	Storage Unit	2	4
Globalstar (16 bit)	52	104	Sky 2A (MCI)	1	2	Astrolink 1-4	4	8
GOES L, M	2	4	Telstar 8-9 (Skynet)	<u>3</u>	<u>6</u>	Coriolis	1	1
Intelsat 901	1	4				AEHF (Bus)	5	10
NSTAR A,B	2	4				GENESIS	1	2
SS/L DBS-2	1	2				MIRO	1	2
PAS 6 - 8	3	6				MSL	1	2
Sirius 3 - CD Radio	3	6				Muses-C	1	2
Sky 1A (MCI)	1	2				SIRTF	1	4
Telstar 5-7 (Skynet)	3	6				Solstice/VCL	2	3
TEMPO 2	1	<u>2</u>				SWIFT	1	4
16 Bit Computers	74	155	<u>16 Bit Computers</u>	12	26	Solar X-Ray	1	2
Deep Space 1	1	1	ETS-8	1	4	TES	1	2
FAISat	1	1	Globalstar (32 bit)	4	8	TRIANA	1	3
Fuse	1	1	Gravity Probe B	1	9	DRP	1	4
Globalstar (32 bit)	52	104	HESSI	1	1	X-2000	5	20
Mars Odyssey	1	2	HIRDLs	1	2	AEHF (Payload)	5	30
MightySat 1	1	1	MightySat 2	1	1	Athena	1	1
Orbiter/Lander -X	3	7	C/NOFS	1	1	Classified	12	16
Mars Pathfinder	1	1				CloudSat	1	2
LMA (STEX, Stardust)	2	4				Deep Impact	1	2
TSX-5	1	1				Discovery	4	5
RAD6000 Computers	64	123	RAD6000 Computers	10	26	Mars 03 Micro Miss	1	2
						Secchi	1	4
						SBIRS Low	24	100
In Space Today:	86	Satellit	es 278 Computer	s				
	40.0							
Hours on Orbit:	16 B	$\pi - 3.7$	Million RAD6000 - 2.4	Million				
						16 Bit RA	D6000	RA





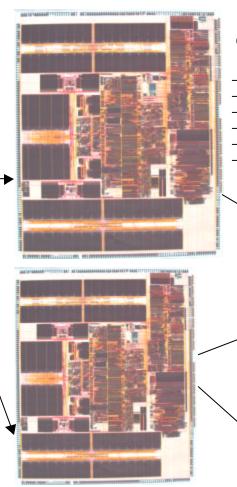
- The Environment
- Effect of Technology Migration
- Mitigation Schemes and Penalties
- Radiation Hardened Processors for Space
- Space Processor Roadmap
- Conclusion

RAD750 Forward Plan Options (2002-2006)



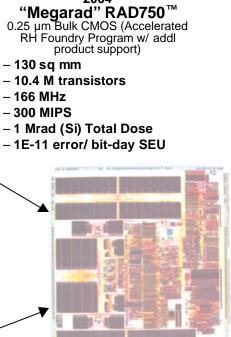
2002 RAD750[™] (pass 2) 0.25 μm Bulk CMOS (Comm'l Foundry) (Budgeted in '02)

- 130 sq mm
- 10.4 M transistors
- 166 MHz
- 300 MIPS
- 200 Krad (Si) Total Dose
- 1E-11 error/ bit-day SEU

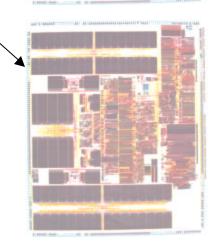


2003 RAD750[™] 0.18 μm Bulk CMOS (Comm'l Foundry-w/ add'l product support)

- est. 90 sq mm
- 10.4 M transistors
- est .200 MHz
- 366 MIPS
- 200 Krad (Si) Total Dose
- 1E-11 error/ bit-day SEU



2004



BAE SYSTEMS

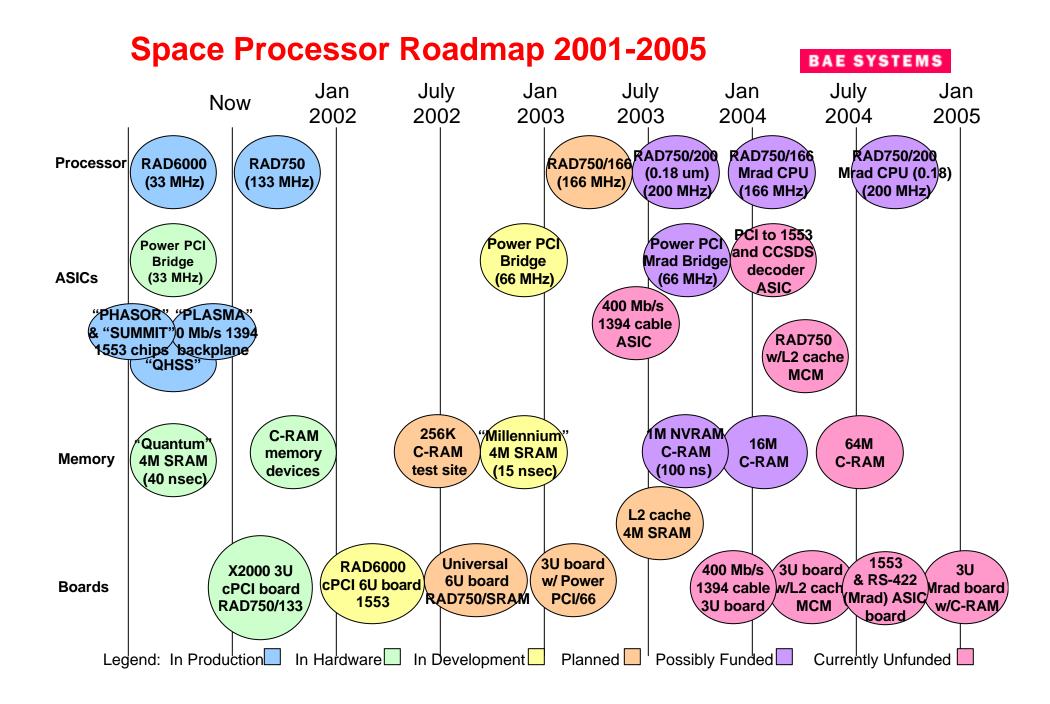
2005 "Megarad" RAD750™

0.18 µm Bulk CMOS (Accelerated RH Foundry Program w/ prod spt)

- est. 90 sq mm
- 10.4 M transistors
- est. 200 MHz
- 366 MIPS
- 1 Mrad (Si) Total Dose
- 1E-11 error/ bit-day SEU

2006 "Megarad" RAD750[™] 0.18 μm Fully Depleted SOI/ SOS CMOS (Accelerated RH Foundry Program w/ process & product support)

- est. 90 sq mm
- 10.4 M transistors
- est. 250 MHz
- 457 MIPS
- 1 Mrad (Si) Total Dose
- 1E-11 error/ bit-day SEU







- The Environment
- Effect of Technology Migration
- Mitigation Schemes and Penalties
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- Space Processor Roadmap
- Conclusion

What it all Means

- Space microelectronics have to operate in a severe environment
- Users are driven to high performance electronics to address new and expanded applications:
 - Available COTS are very sensitive to space radiation
 - Variation in the radiation environment with orbit and over time is a major consideration in processor selection
 - Mitigation techniques have significant impact on weight, power and performance.
 - Technology scaling results in dramatically increased exposure to Single Event Effects in more modern semiconductor components
- Radiation Hardened Processors offer the best solution
 - Capitalize on massive commercial investment in hardware and software
 - Enhanced for the various environmental issues
 - Offer the best power/performance/mass/volume alternative

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